

Vishay Semiconductors

Silicon PIN Photodiode



DESCRIPTION

VBPW34S and VBPW34SR are high speed and high sensitive PIN photodiodes. It is a surface mount device (SMD) including the chip with a 7.5 mm² sensitive area detecting visible and near infrared radiation.

FEATURES

Package type: surface mount

• Package form: GW, RGW

• Dimensions (L x W x H in mm): 6.4 x 3.9 x 1.2

• Radiant sensitive area (in mm²): 7.5

· High photo sensitivity

• High radiant sensitivity

• Suitable for visible and near infrared radiation

· Fast response times

• Angle of half sensitivity: $\varphi = \pm 65^{\circ}$

• Floor life: 168 h, MSL 3, acc. J-STD-020

· Lead (Pb)-free reflow soldering

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

· High speed photo detector

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.1} (nm)	
VBPW34S	55	± 65	430 to 1100	
VBPW34SR	55	± 65	430 to 1100	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
VBPW34S	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Gullwing		
VBPW34SR	Tape and reel	MOQ: 1000 pcs, 1000 pcs/reel	Reverse gullwing		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	60	V	
Power dissipation	T _{amb} ≤ 25 °C	P _V	215	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	Acc. reflow solder profile fig. 8	T _{sd}	260	°C	
Thermal resistance junction/ambient		R _{thJA}	350	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

Silicon PIN Photodiode



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	60			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		2	30	nA
Diada sanaitana	$V_R = 0 \text{ V, } f = 1 \text{ MHz, } E = 0$	C _D		70		pF
Diode capacitance	$V_R = 3 V, f = 1 MHz, E = 0$	C _D		25	40	pF
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of Vo	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	l _k		50		μΑ
Temperature coefficient of I _k	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}$	TK _{Ik}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2, \ \lambda = 950 \text{ nm}, \ V_R = 5 \text{ V}$	I _{ra}	45	55		μΑ
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λρ		940		nm
Range of spectral bandwidth		λ _{0.1}		430 to 1100		nm
Noise equivalent power	$V_R = 10 \text{ V}, \lambda = 950 \text{ nm}$	NEP		4 x 10 ⁻¹⁴		W/√Hz
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t _r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t _f		100		ns

Note

 T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

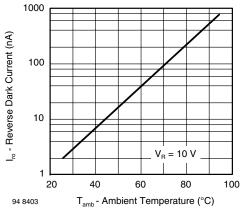


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

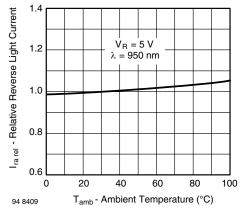


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



Silicon PIN Photodiode

Vishay Semiconductors

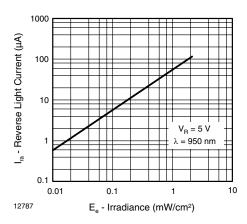


Fig. 3 - Reverse Light Current vs. Irradiance

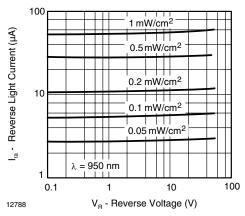


Fig. 4 - Reverse Light Current vs. Reverse Voltage

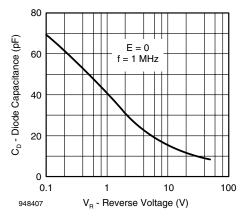


Fig. 5 - Diode Capacitance vs. Reverse Voltage

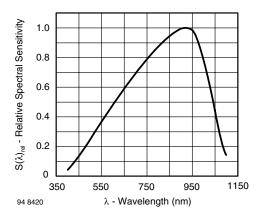


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

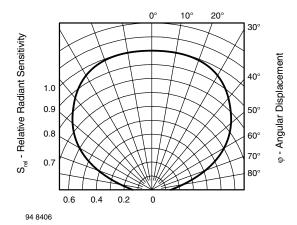


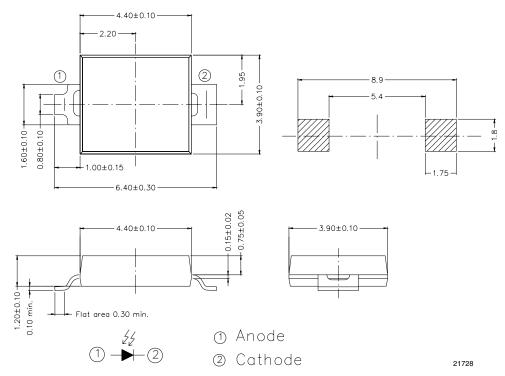
Fig. 7 - Relative Radiant Sensitivity vs. Angular Displacement

Vishay Semiconductors

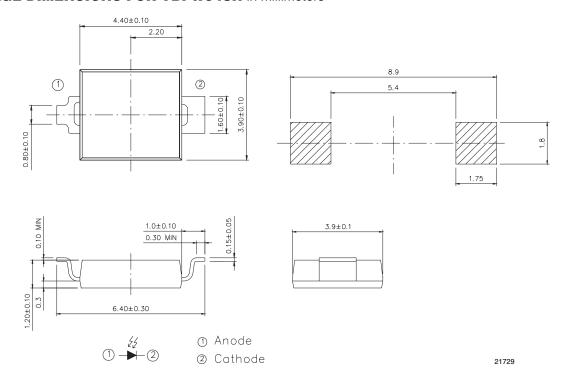
Silicon PIN Photodiode



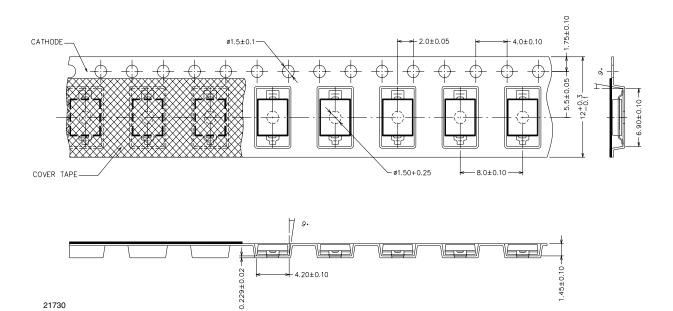
PACKAGE DIMENSIONS FOR VBPW34S in millimeters



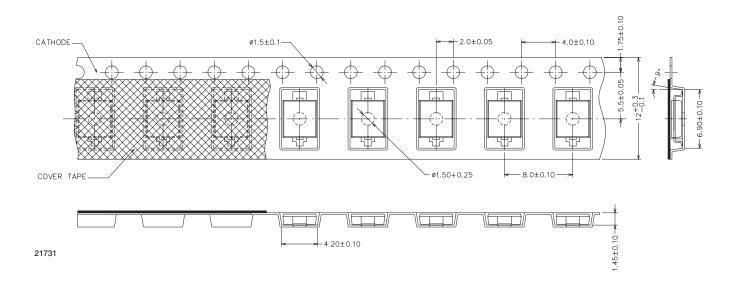
PACKAGE DIMENSIONS FOR VBPW34SR in millimeters



TAPING DIMENSIONS FOR VBPW34S in millimeters

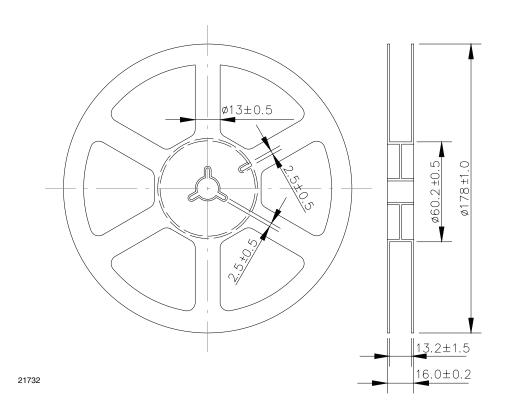


TAPING DIMENSIONS FOR VBPW34SR in millimeters





REEL DIMENSIONS FOR VBPW34S AND VBPW34SR in millimeters



SOLDER PROFILE

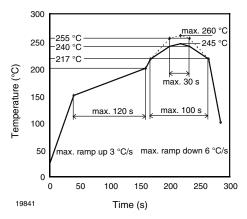


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

Floor life: 168 h

Conditions: T_{amb} < 30 °C, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or recommended conditions:

192 h at 40 °C (+ 5 °C), RH < 5 %

or

96 h at 60 °C (+ 5 °C), RH < 5 %.



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08